# **ECH8310**

# ON Semiconductor®

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# P-Channel Power MOSFET -30V, -9A, 17mΩ, Single ECH8

# **Features**

- · 4V drive
- · Halogen free compliance
- · Protection diode in

# **Specifications**

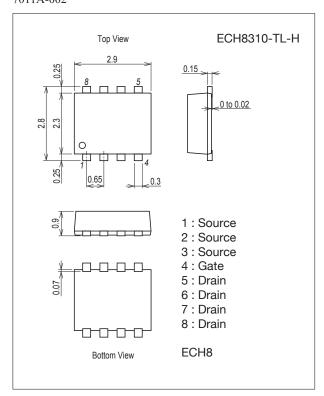
# **Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-9	Α
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-60	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# **Package Dimensions**

unit : mm (typ) 7011A-002



# **Product & Package Information**

• Package : ECH8

• JEITA, JEDEC :-

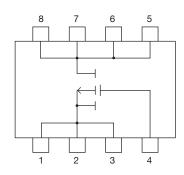
• Minimum Packing Quantity : 3,000 pcs./reel

# Packing Type: TL



Marking

## **Electrical Connection**



# ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

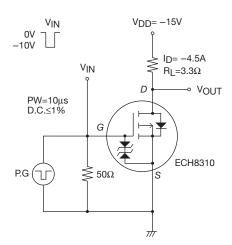
# **ECH8310**

# **Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Parameter		Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>G</sub> S=0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4.5A		12		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-4.5A, VGS=-10V	9	13	17	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =-2A, V <sub>G</sub> S=-4.5V	12	20	28	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-2A, V <sub>G</sub> S=-4.0V	13.5	23	32.5	mΩ
Input Capacitance	Ciss			1400		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		350		pF
Reverse Transfer Capacitance	Crss			250		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			10		ns
Rise Time	t <sub>r</sub>	0 " 17 10" "		45		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		134		ns
Fall Time	tf			87		ns
Total Gate Charge	Qg			28		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-9A		4		nC
Gate-to-Drain "Miller" Charge	Qgd	1		6		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-9A, V <sub>GS</sub> =0V		-0.8	-1.2	V

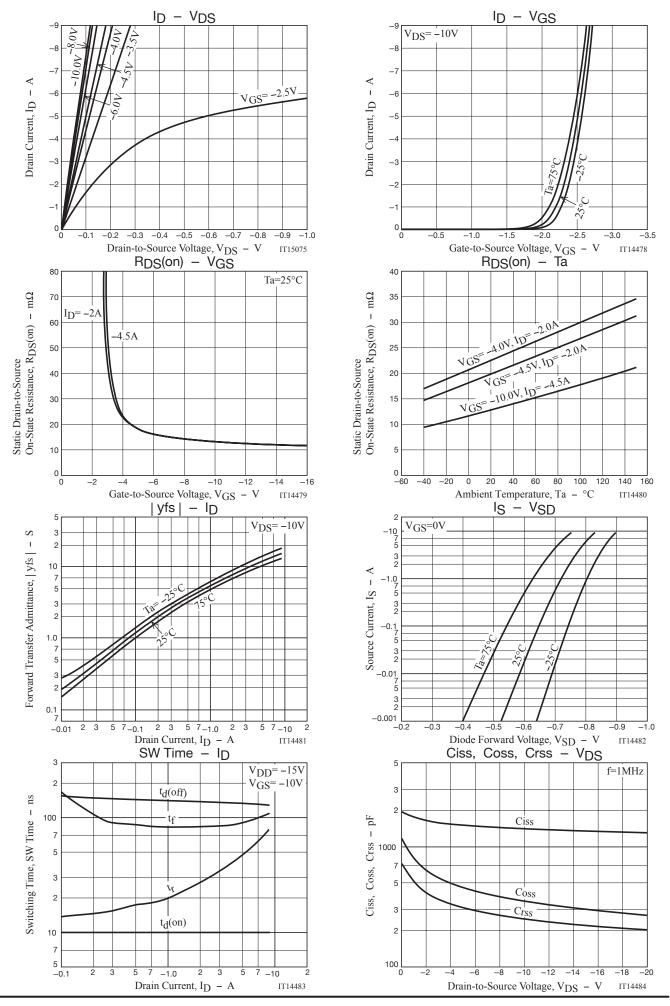
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

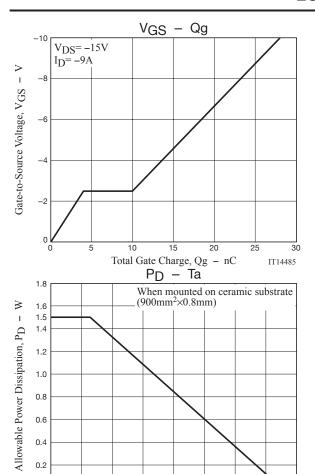
# **Switching Time Test Circuit**



# **Ordering Information**

Device	Package	Shipping	memo	
ECH8310-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free	





0.2

0

20

60

80

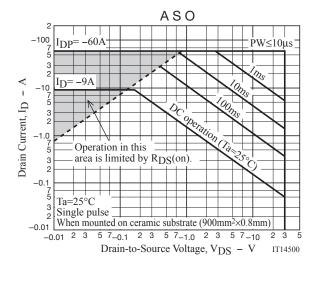
Ambient Temperature, Ta - °C

100

140

160

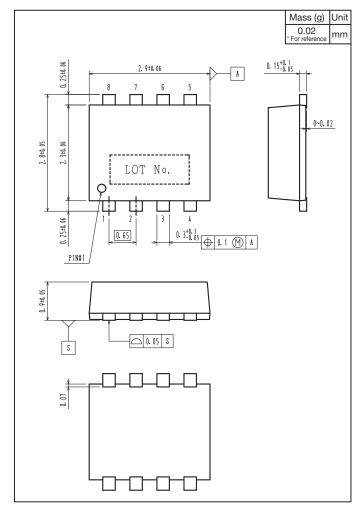
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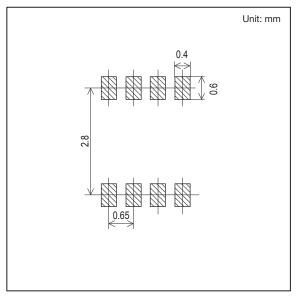


# **Outline Drawing**

ECH8310-TL-H

# **Land Pattern Example**





Note on usage: Since the ECH8310 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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